

# An Overview of Utility and Mechanisms of Photonics for Power Electronics

## Invited Lecture

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**ARPA-E Workshop: Ultra-Fast-Triggered Semiconductors for Enhanced System Resiliency**

Washington DC

October 6-7, 2022

Acknowledgements:

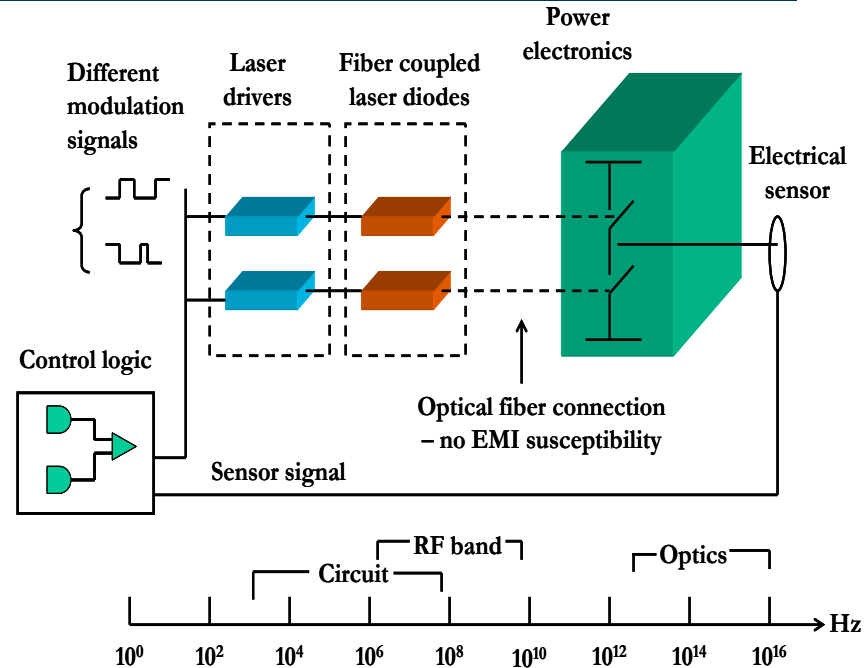
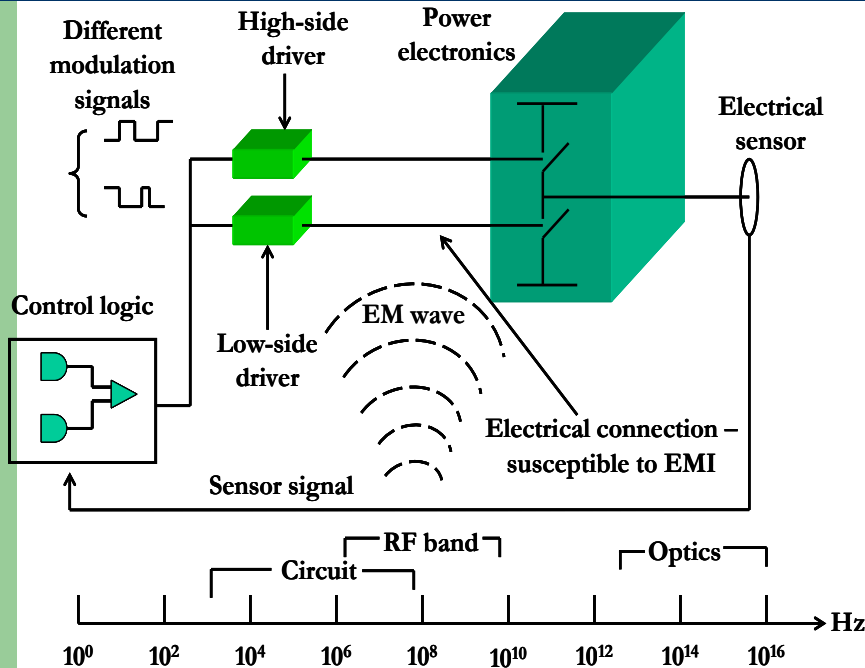
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DOE, LLNL, UIC

## Disclaimer

The content of this presentation is covered by the following intellectual properties:

1. S.K. Mazumder, “Photonicallly activated single bias fast switching integrated thyristor”, U.S. Patent Application# 13281207, filed in 2011.
2. S.K. Mazumder and T. Sarkar, “Optically-triggered multi-stage power system and devices”, U.S. Patent Number 8183512, awarded on May 22, 2012.
3. S.K. Mazumder and T. Sarkar, “Optically-triggered power system and devices”, USPTO Patent# 8,294,078, awarded on October 23, 2012.
4. X. Wang, S.K. Mazumder, and W. Shi, “Insulated-gate photoconductive semiconductor switch”, USPTO Patent# 9543462 B2, awarded on January 10, 2017.

# Utility of Photonics for Power Electronics (PE) [1], [2]



- Immunity from internal/external electromagnetic interference (EMI)
- Electrical isolation between power and control stages (no backpropagation)
- No need for complex floating electrical gate drivers
- Reduced device triggering delay
- Addressing issues with n&p type suitable doping for WBG/UWBG power sem. devices
- Removes requirement for high quality gate dielectrics for power sem. devices
- Dynamic modulation of device switching transition dynamics feasible with minimal excitation effort and selective excitation

# Some Utility (Application) of Photonic PE:

## *Power Grid (HV/MV)*

**Static Var  
Compensator (SVC)**



**High Voltage Direct  
Current (HVDC)**



**StatCom**



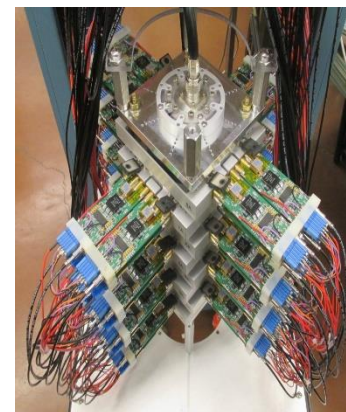
**Solid-State  
Transformer**



**Solid-State Fault  
Current Limiter**

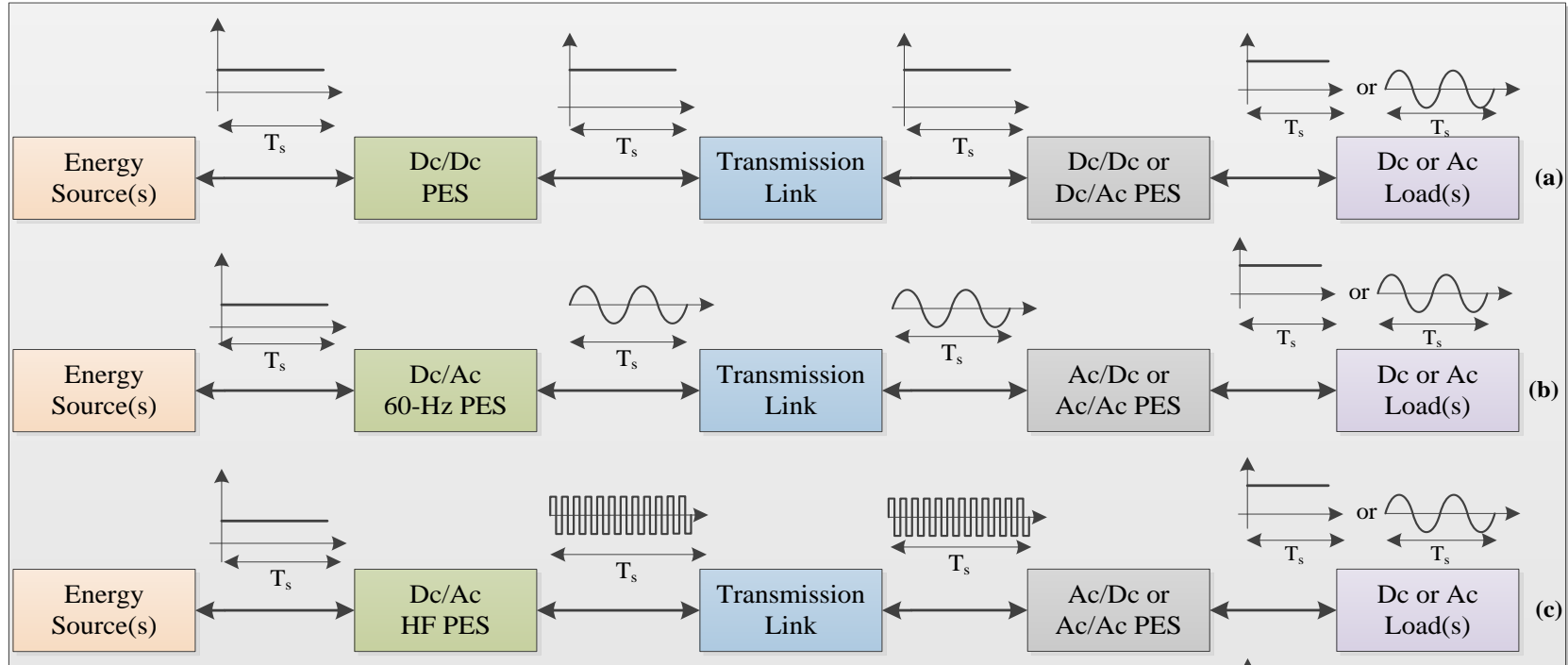


**Pulsed Power  
System**



# Some Utility (Application) of Photonic PE: Discretized HF Power Transfer (LV/MV) (Patented) [3]-[5]

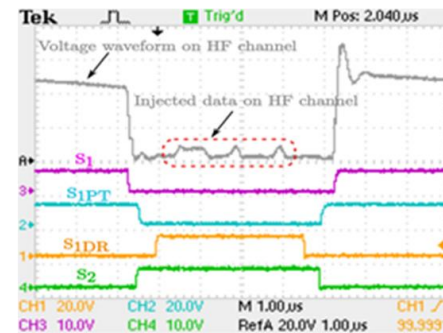
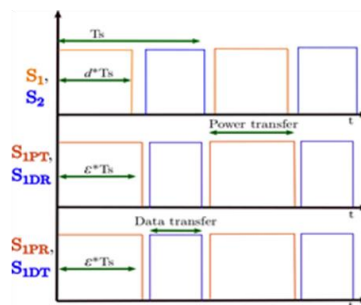
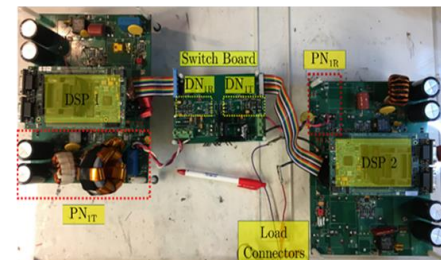
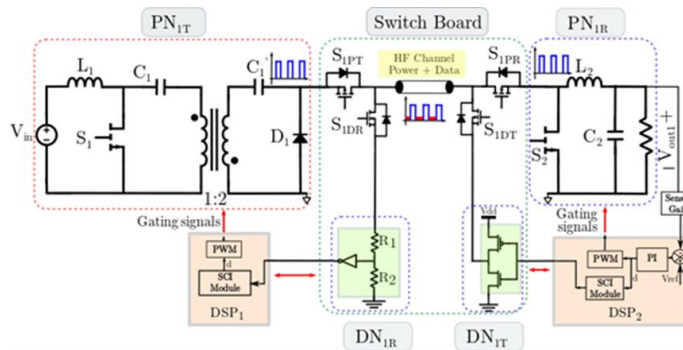
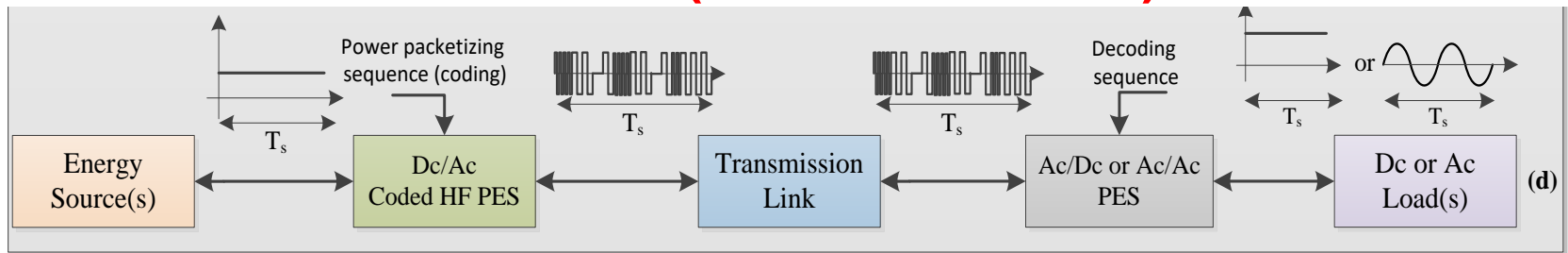
## Traditional Power Transfer



# Some Utility (Application) of Photonic PE:

## Discretized HF Power Transfer (LV/MV) (Patented) [3]-[5]

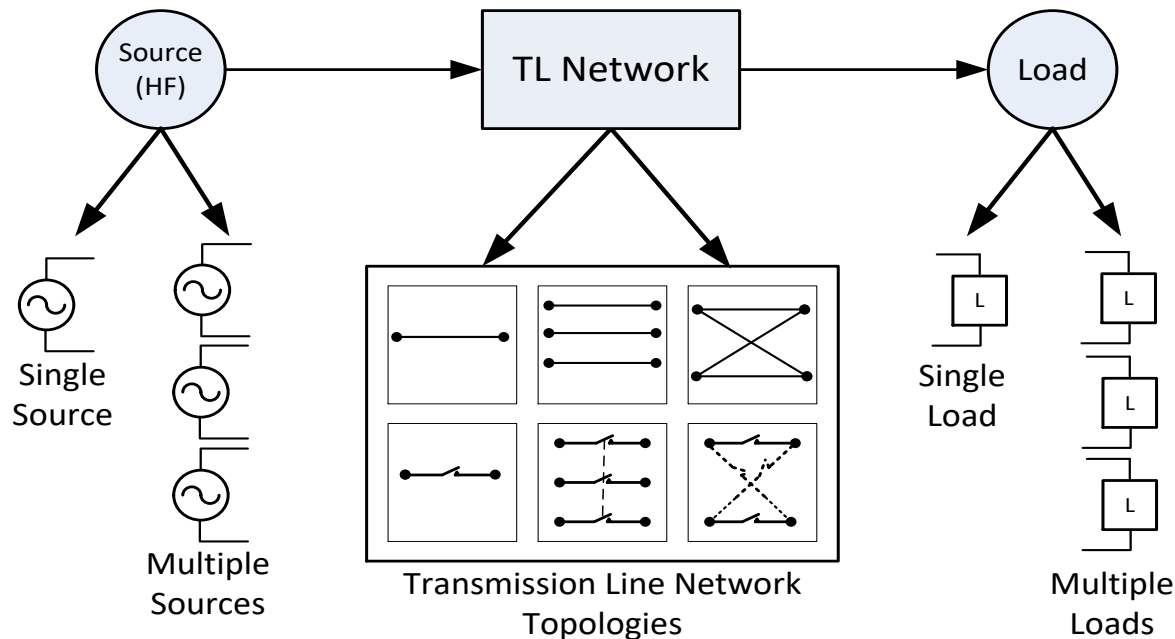
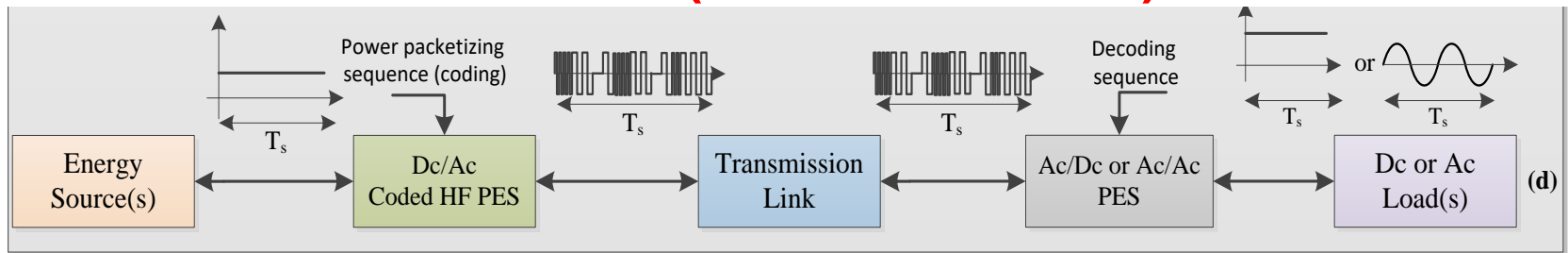
### Coded Asynchronous Multi-Scale High Frequency Power Transfer (Patent Protected)



# Some Utility (Application) of Photonic PE:

## *Discretized HF Power Transfer (LV/MV) (Patented) [3]-[5]*

### Coded Asynchronous Multi-Scale High Frequency Power Transfer (Patent Protected)





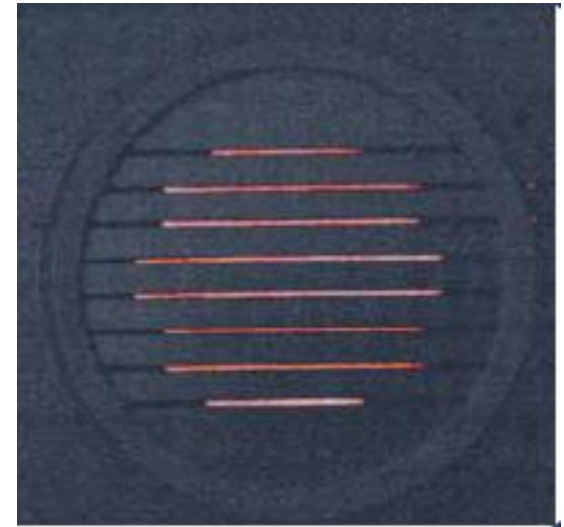
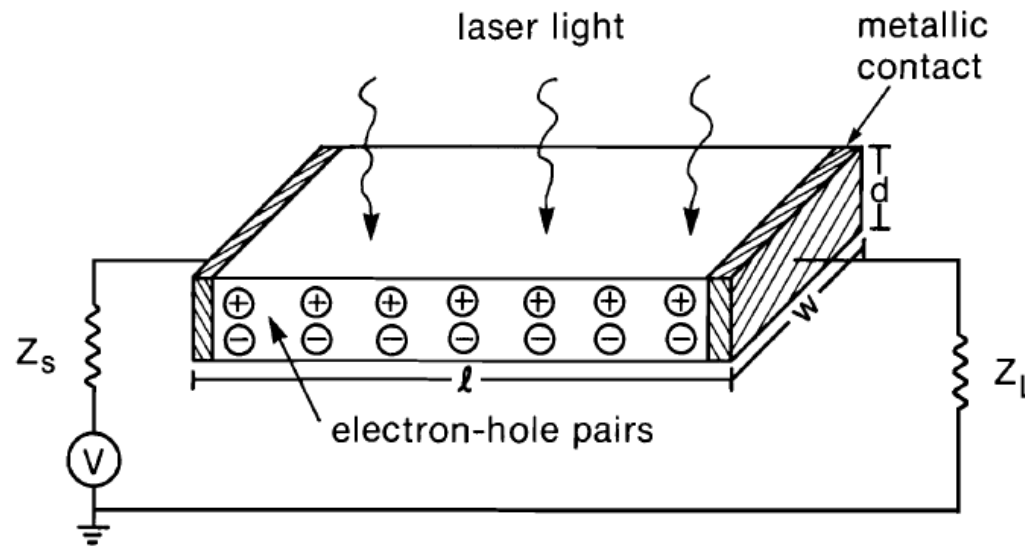
# Requirements of PE from (Optical) Power Semiconductor Devices (PSDs)

- ☐ Low cost
- ☐ Low leakage
- ☐ Low on-state drop
- ☐ Low optical power
- ☐ Moderate to high repetition rate
- ☐ Wide variation in duty cycle
- ☐ Fast switching dynamics
- ☐ Reduced  $dv/dt$  and  $di/dt$  stress
- ☐ High reliability (electrical, mechanical, thermal stabilities)
- ☐ Low device complexity
- ☐ Low drive complexity



# Mechanisms of Optical PSD: *Low Rise Time [6]*

## PCSS



- High speed device turn on
- Minimum light activation to actuation delay
- Relatively simple device structure
- No gate dielectric
- Triggering efficiency low
- Triggering cost could be high
- Duty cycle typically small
- Current filamentation problem

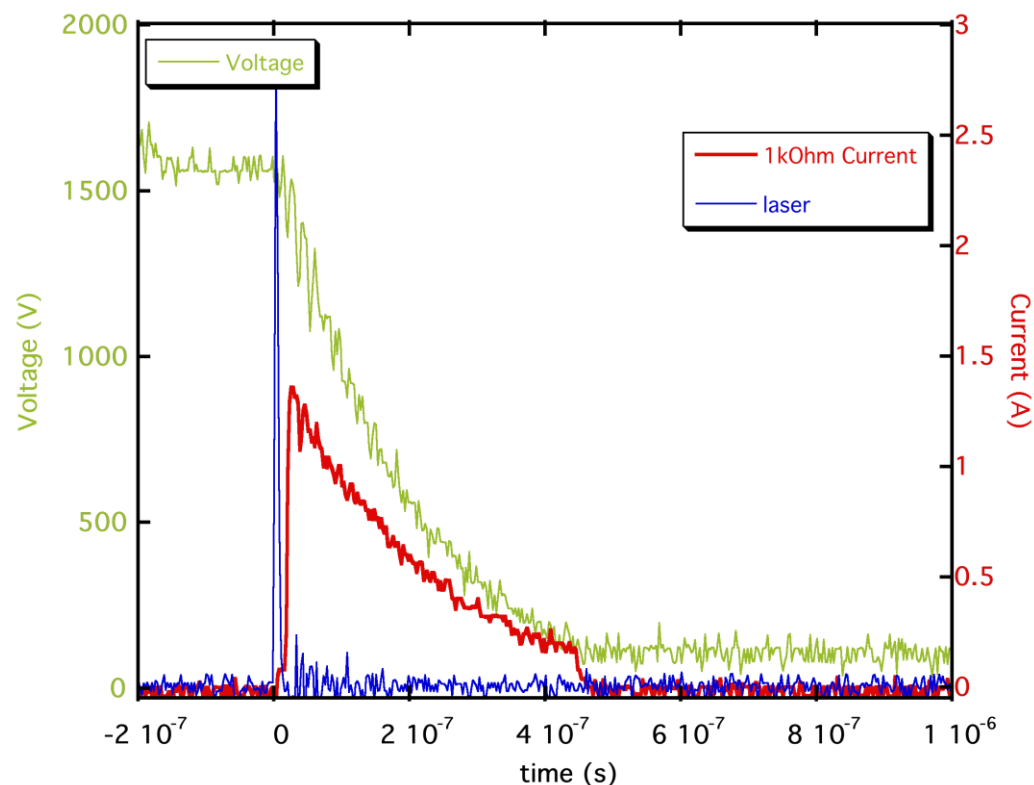
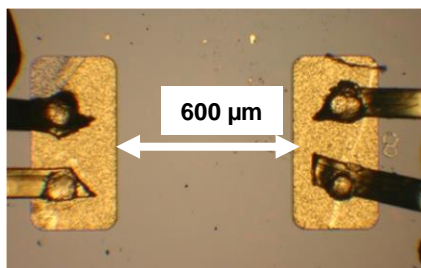
# Mechanisms of Optical PSD: *Low Rise Time with Reduced Optical Power and/or Cost* [7]-[9], [13], [14]

## GaN PCSS

Cross-Section Diagram of GaN PCSS



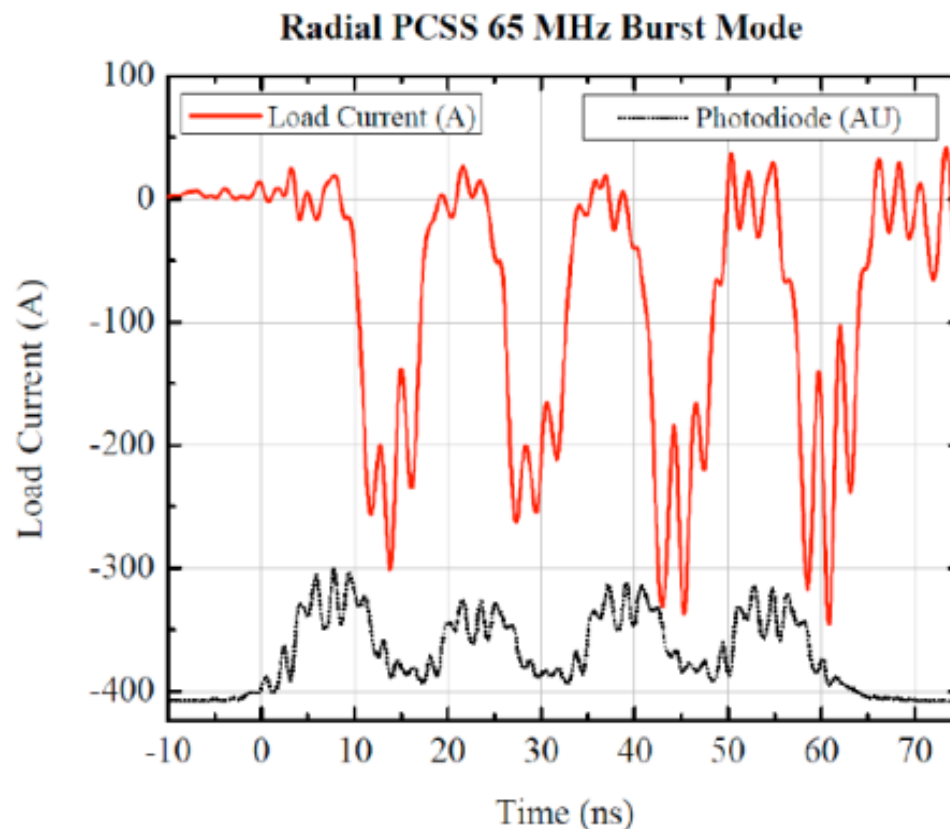
Optical Image (top view) of GaN PCSS



# Mechanisms of Optical PSD: *Low Rise Time with Reduced Optical Power and/or Cost [7]-[9], [13], [14]*



Vertical PCSS switch capable of holding-off up to 50 kV

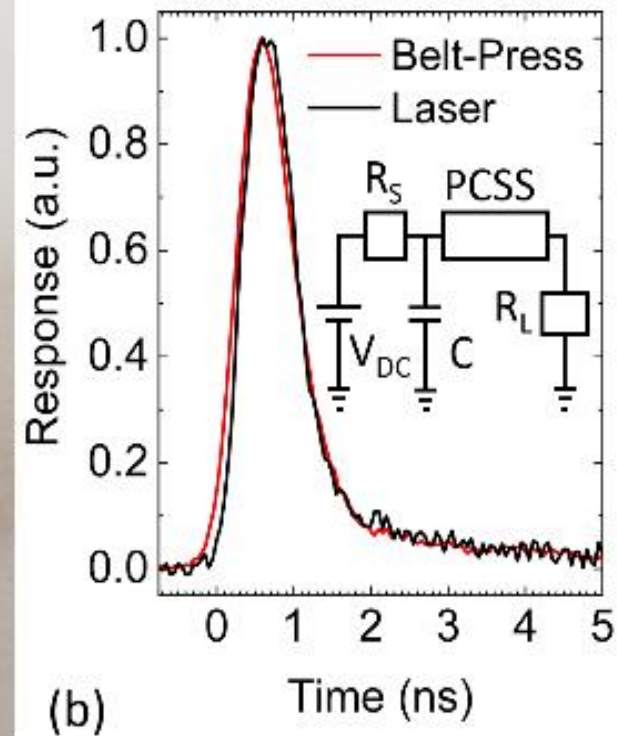
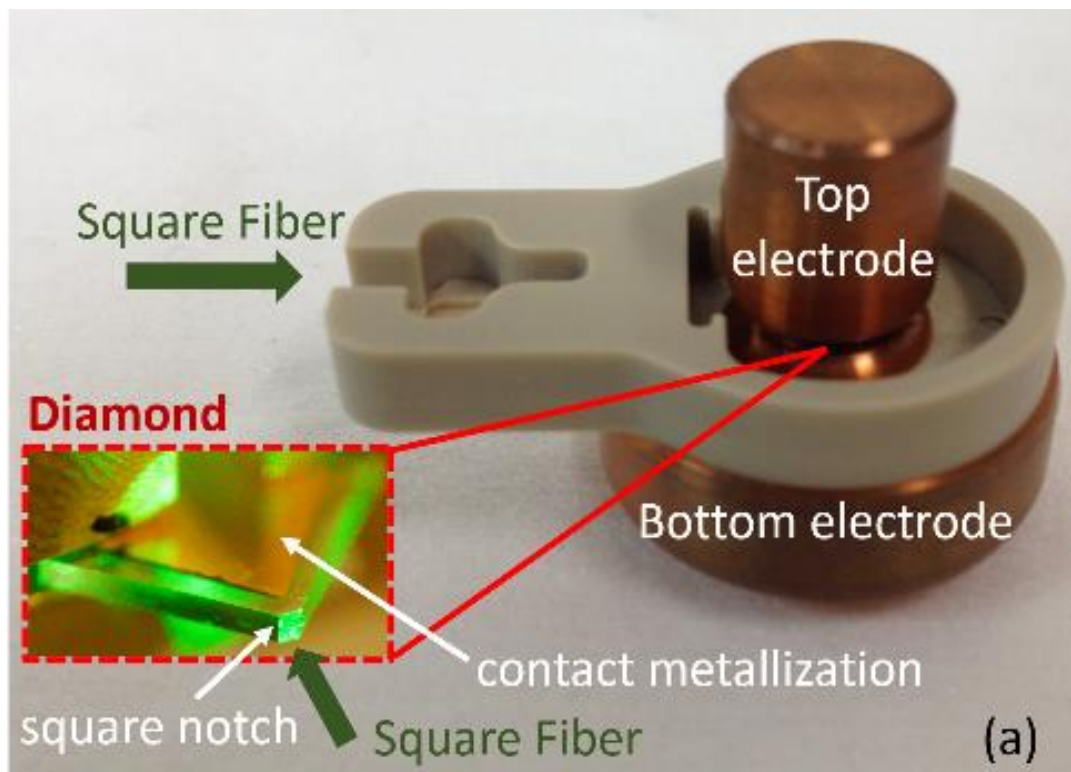


20 kV 65 MHz burst mode switching into 50  $\Omega$



# Mechanisms of Optical PSD: *Low Rise Time with Reduced Optical Power and/or Cost* [7]-[9], [13], [14]

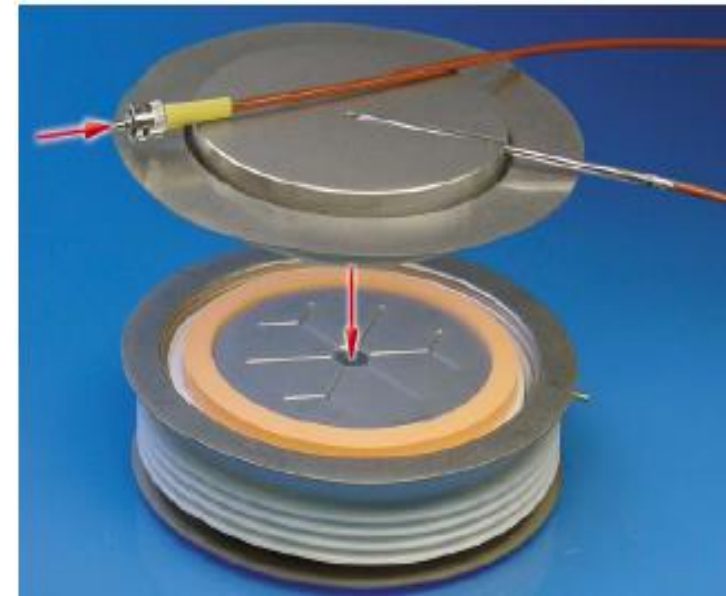
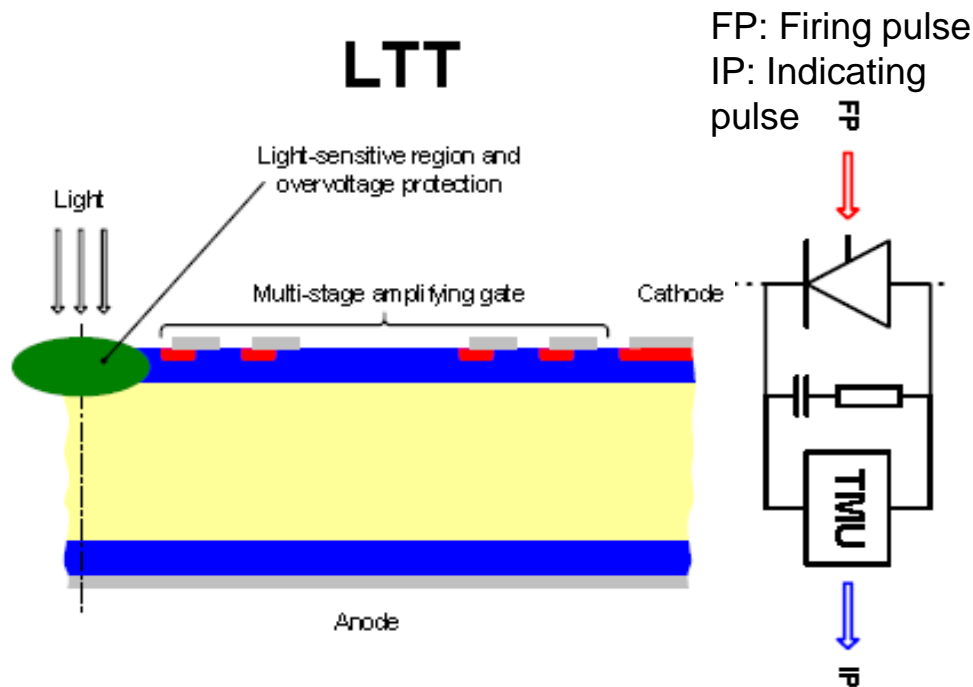
## UWBG (Diamond) PCSS



- Higher speed device turn on
- Mid-bandgap laser reduces cost

- Enhanced device cost
- Reduced laser utilization

# Mechanisms of Optical PSD: *Low Optical Power [6]*



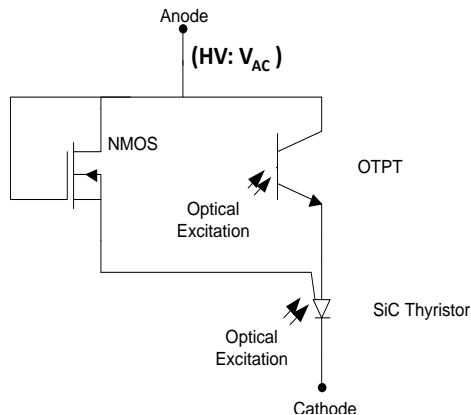
- Smooth turn on
- High device gain
- Very low optical triggering power due to pilot thyristor
- Device real-time status available

- Turn off is slow
- Gate drive is complex and lossy since it has to handle large turn-off current
- Integrated device structure complex



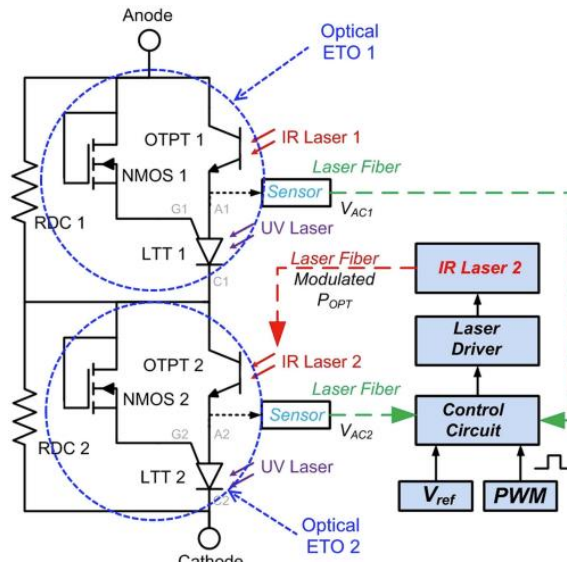
# Mechanisms of Optical PSD: *Low Optical Power and Faster Switching [6],[10],[11]*

## SiC Optical ETO (UIC)



- No control bias required
- MF operation feasible
- Different materials can be used
- Dynamic modulation possible
- Series connection possible

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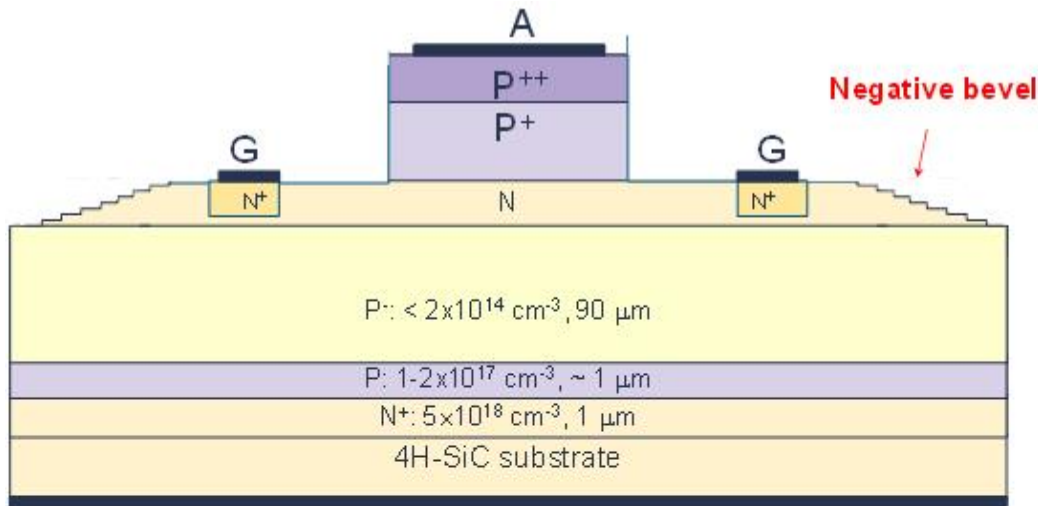
**Series  
Connection**



# Mechanisms of Optical PSD:

*Low Optical Power and Faster Switching [6],[10],[11]*

LESES



### SiC 12-kV Thyristor Structure with Beveling

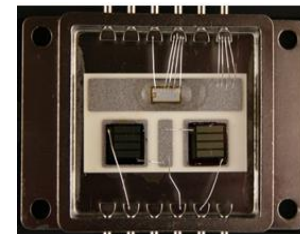
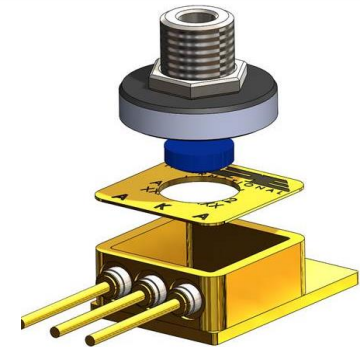
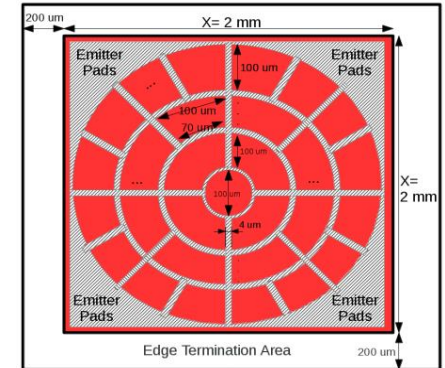


## SiC VHV Thyristor Die



## SiC VHV Thyristor Module

Acknowledgement: ARL, SPC



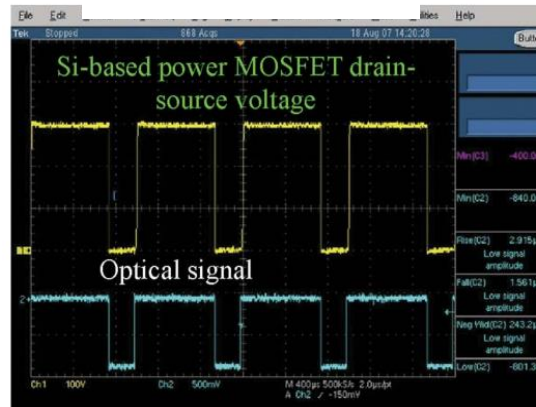
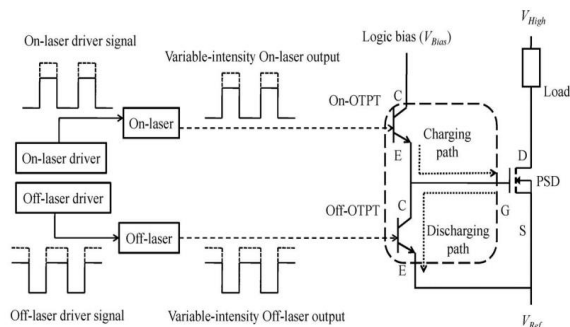
# OTPT

*Acknowledgement: UIC*

### Acknowledgement: Cree, Silicon Power

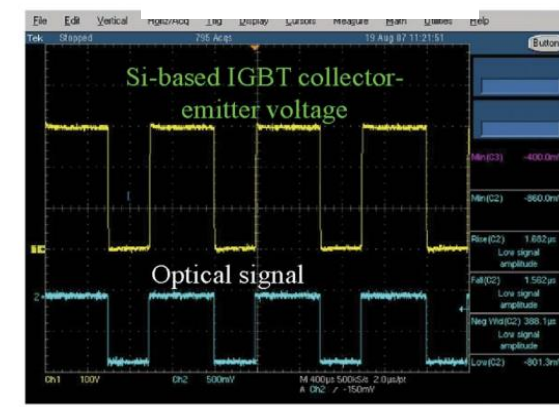
# Mechanisms of Optical PSD: *Optical Gate Driven Insulated Gate PSD [12]*

## Si MOSFET

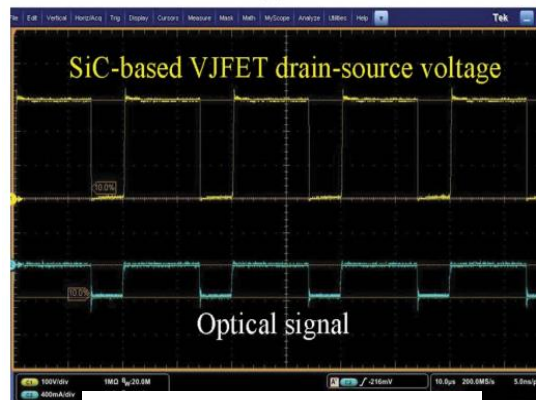
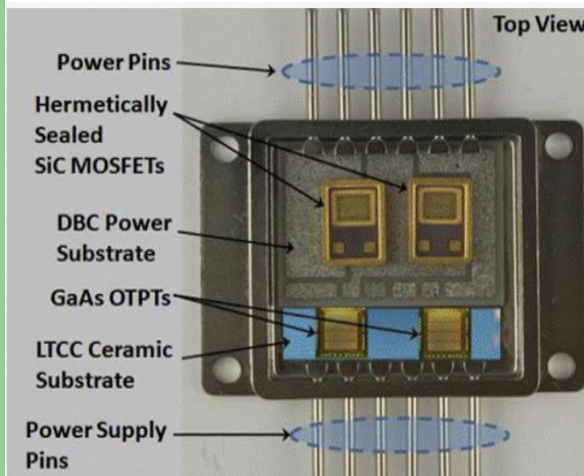


(a)

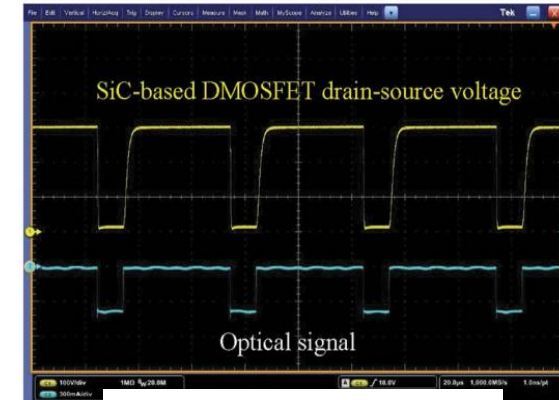
## Si IGBT



(b)



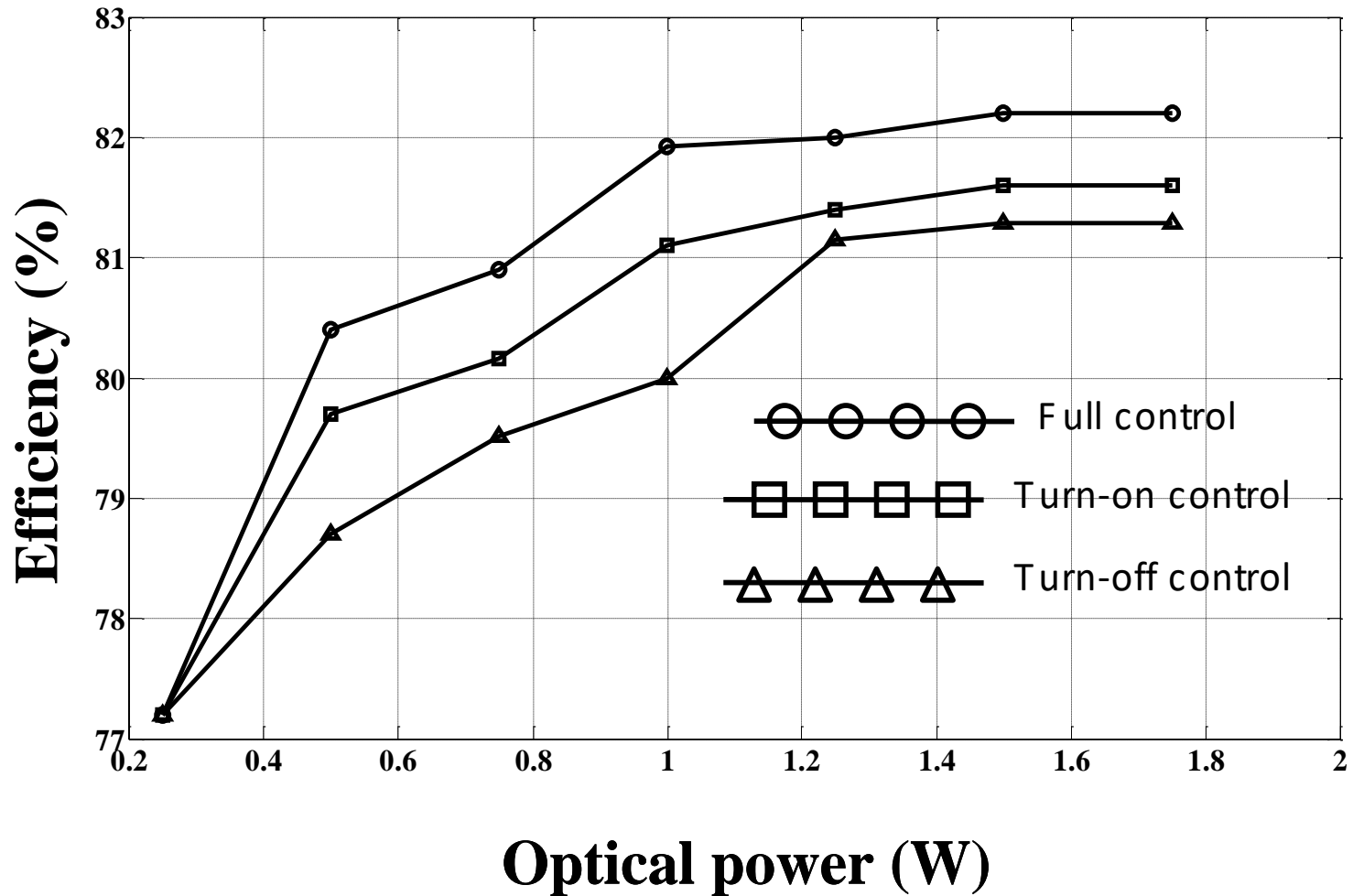
## SiC VJFET



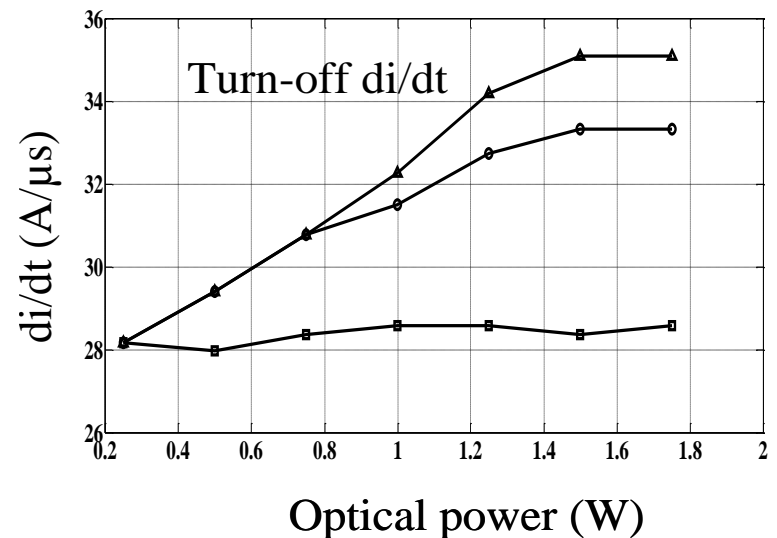
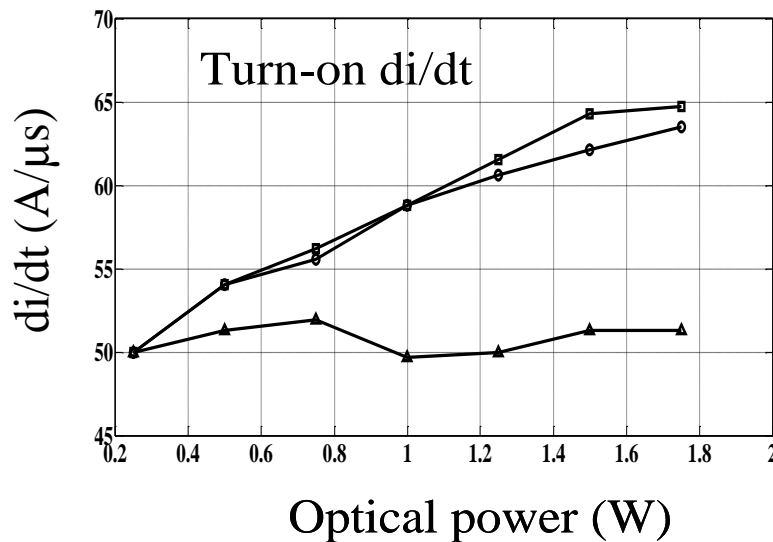
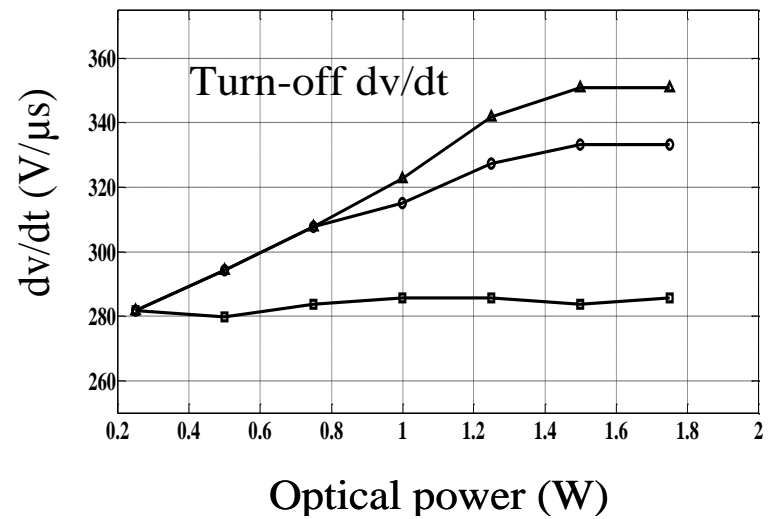
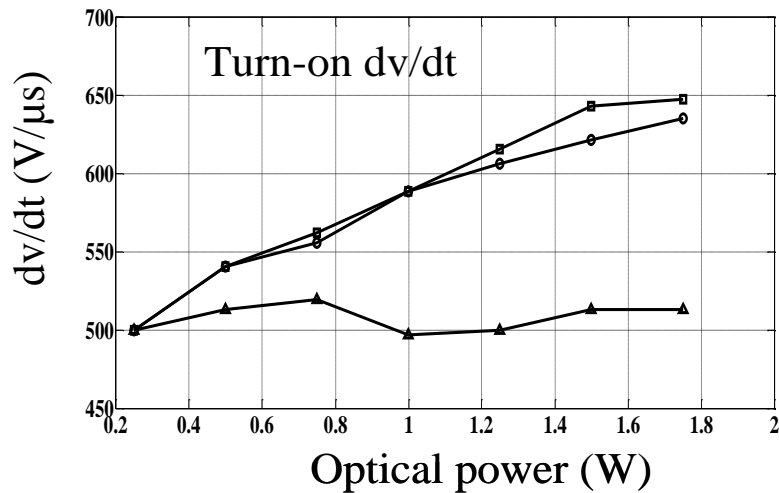
## SiC MOSFET

- Triggering wavelength is unchanged
- Separation of power and control
- Higher onset delay
- No direct photogeneration

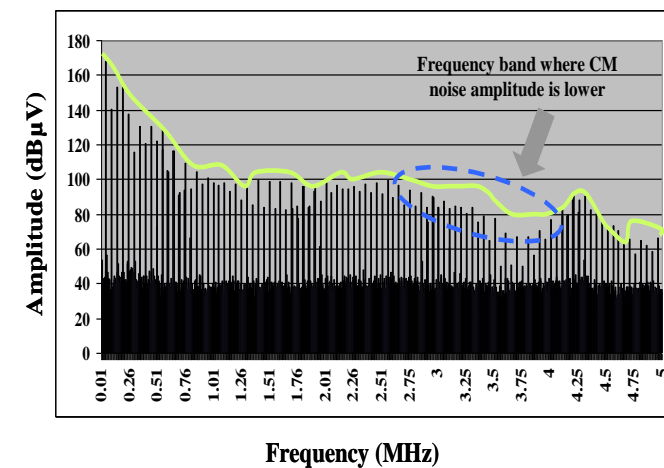
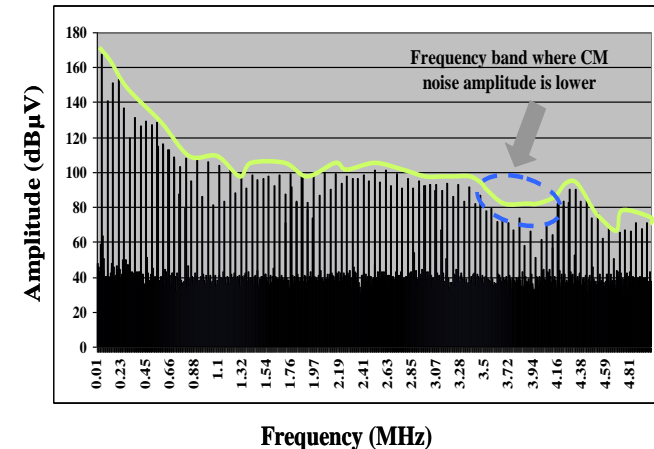
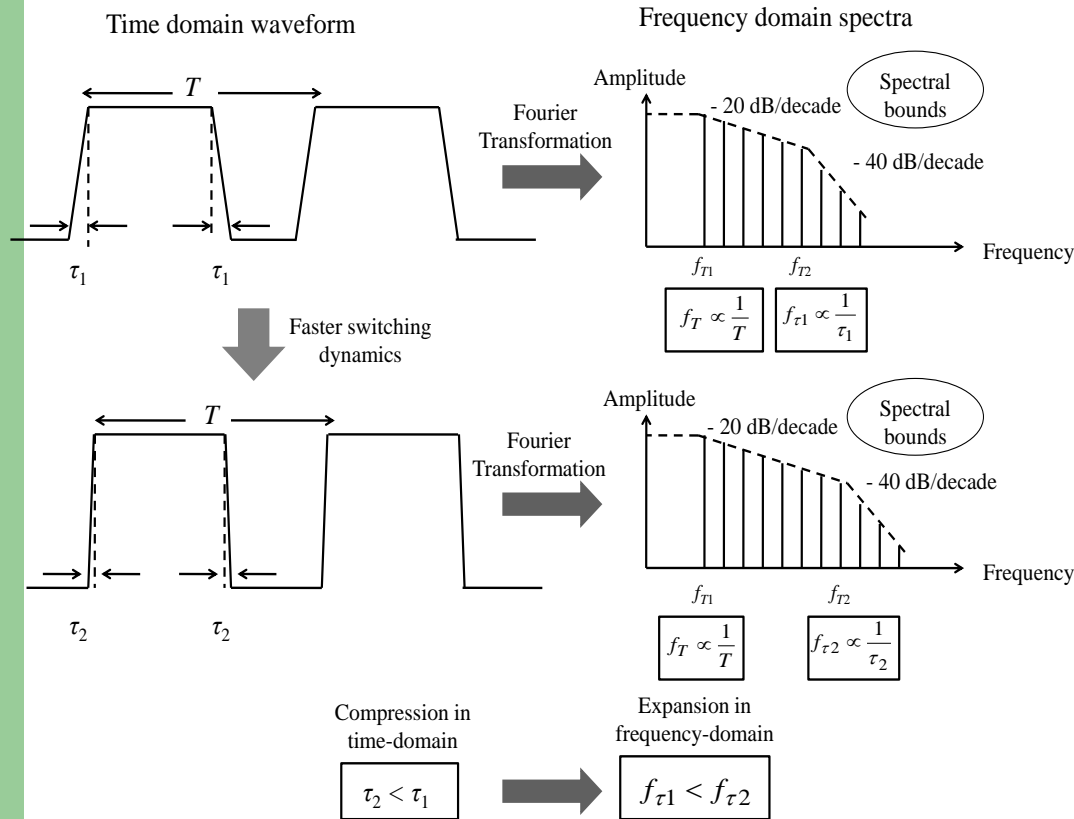
# Mechanism for Optical Control: *Experimental Illustrations [12]*



# Mechanism for Optical Control: *Experimental Illustrations [12]*



# Mechanism for Optical Control: *Experimental Illustrations [12]*



## Summary

1. Optically-controlled PSDs yield several device and system level advantages which can have direct impact on the reliability, efficiency, simplicity, controllability, and form factor of the PE based next-generation energy system / grid.
2. Innovative photonic MV/HV PSDs that leverage several superior properties of UWBG/WBG materials to yield key performance metrics (e.g., high gain, low leakage, low loss, low rise/fall times, wide duty cycle etc.) and support the goals of PESs outlined in “1” are a necessity.
3. A key aspect of that device-system connectivity, depends on how these optical UWBG/WBG PSDs are innovatively controlled to mitigate their impacts on the system environment and vice-versa and achieve multi-scale optimality of the next-generation PES.



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# Thank You!

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